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NAGAHAMA et al.

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U.S. PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS

OTHER DOCUMENTS (including Author, Title, Date, Pertinent pages, etc.)

Nakamura et al: "High-power, Long-Lifetime InGaN/GaN/AlGaN-Based Laser Diodes Grown on Pure GaN Substrates," *Jpn J. Appl. Phys.*, Vol. 37 (1998) pp. 309-312

*Examiner

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